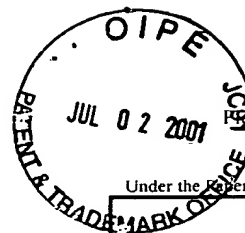


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TRANSMITTAL FORM <i>(to be used for all correspondence after initial filing)</i>	Application Number	09/327,469	
	Filing Date	June 8, 1999	
	First Named Inventor	Shunpei YAMAZAKI	
	Group Art Unit	2814	
	Examiner Name	Ginette PERALTA	
Total Number of Pages in This Submission		Attorney Docket Number	740756-1982

ENCLOSURES (check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/ Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group
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740756-1982

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI

Application No.: 09/327,469

Filed: June 8, 1999

For: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING
THE SAME

) Art Unit: 2814
)
)

) Examiner: Ginette PERALTA
)
)

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AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

June 28, 2001

Dear Sir:

In response to the Examiner's non-Final Office Action mailed March 28, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claim 1 without prejudice or disclaimer of the subject matter disclosed therein.

Please amend claims 2, 3, 9, 10, 20, and 21 as follows:

2. (Amended) A method of manufacturing a semiconductor device, comprising:
- a first step of forming a semiconductor film;
 - a second step of holding a catalytic element that promote the crystallization of said semiconductor film in contact with said semiconductor film; and
 - a third step of irradiating a laser beam shaped in a rectangle or a square while moving the laser beam from one side of said semiconductor film toward another side thereof to sequentially crystallize said semiconductor film to form a crystalline semiconductor film,